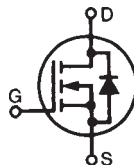


PolarHV™ Power MOSFET

IXTA 8N50P
IXTP 8N50P

$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 8 \text{ A} \\ R_{DS(on)} &\leq 0.8 \Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated

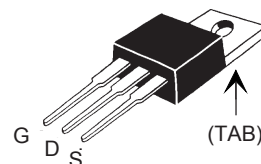


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	8	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	14	A
I_{AR}	$T_C = 25^\circ\text{C}$	8	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	400	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 18 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	150	W
T_J		$-55 \dots +150$	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		$-55 \dots +150$	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	3	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

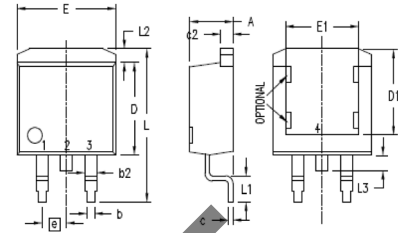
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 100 \mu\text{A}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			50 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.8 Ω

Symbol	Test Conditions	Characteristic Values (T _j = 25° C unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , pulse test	5	8	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1050	pF
C_{oss}			120	pF
C_{rss}			12	pF
$t_{d(on)}$	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = I _{D25} R _G = 18 Ω (External)		22	ns
t_r			28	ns
$t_{d(off)}$			65	ns
t_f			23	ns
$Q_{g(on)}$	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		20	nC
Q_{gs}			7	nC
Q_{gd}			7	nC
R _{thJC}	(TO-220)		0.25	0.83° C/W
R _{thCS}				° C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T _j = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
I _S	V _{GS} = 0 V			8 A
I _{SM}	Repetitive			14 A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t _{rr}	I _F = 8 A, V _{GS} = 0 V, V _R = 100 V -di/dt = 100 A/μs		400	ns

TO-263 (IXTA) Outline



1. GATE
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR) BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXTP) Outline

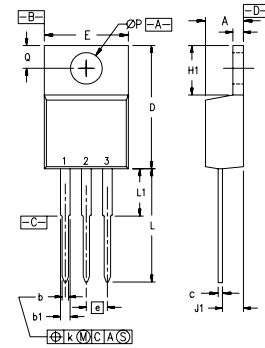


Fig. 1. Output Characteristics
@ 25°C

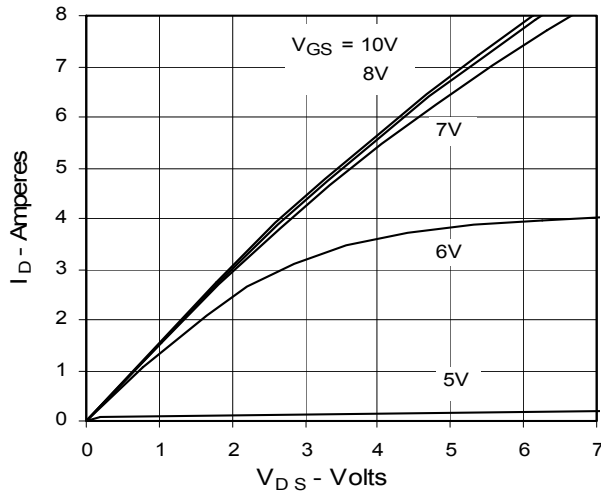


Fig. 2. Extended Output Characteristics
@ 25°C

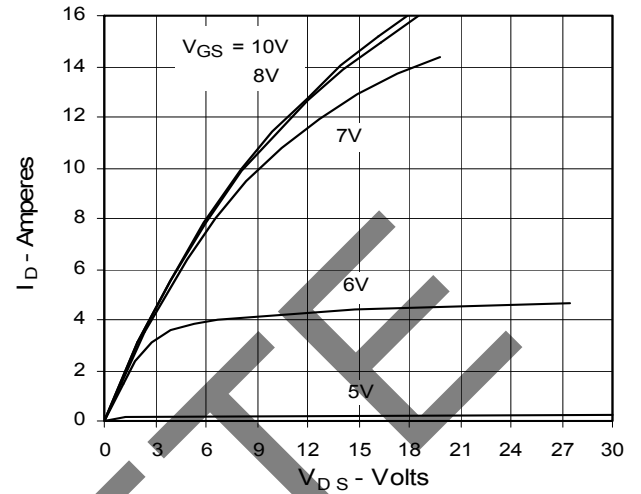


Fig. 3. Output Characteristics
@ 125°C

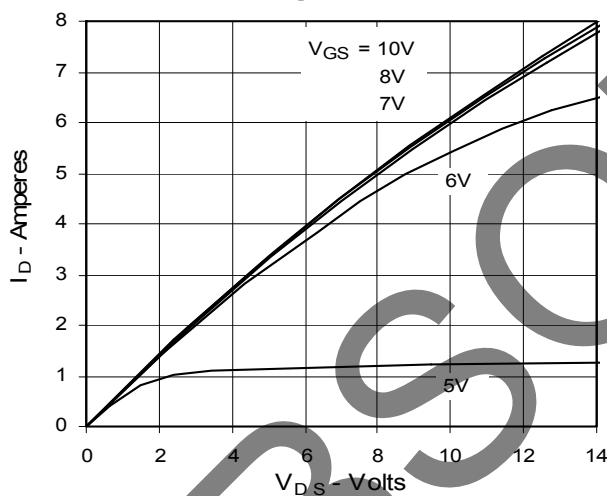


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

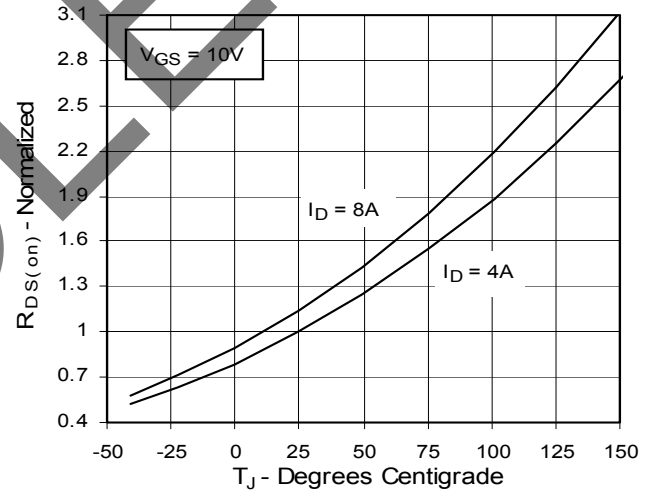


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

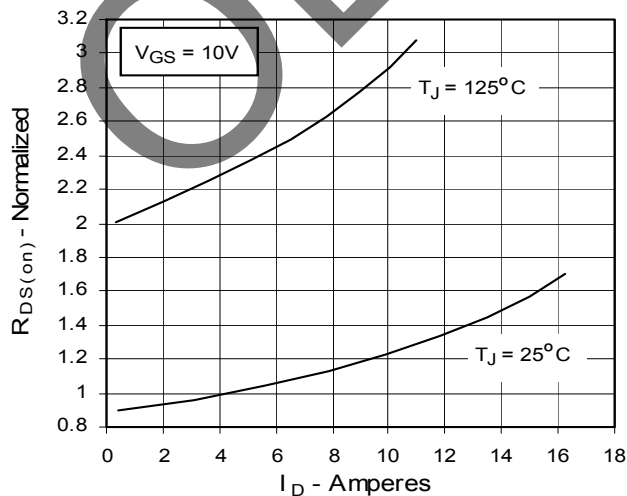


Fig. 6. Drain Current vs. Case Temperature

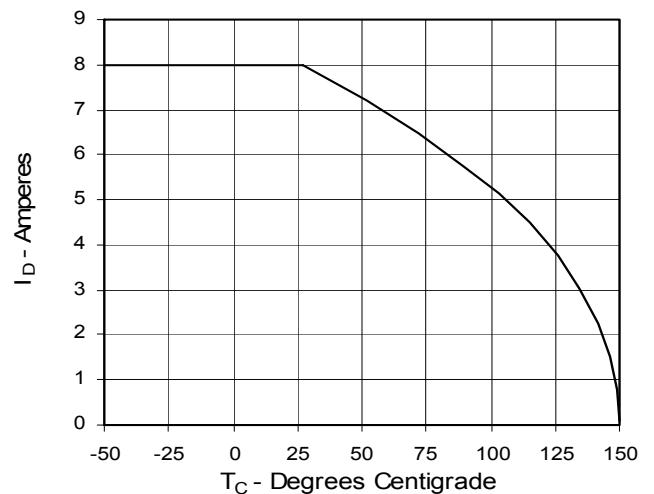


Fig. 7. Input Admittance

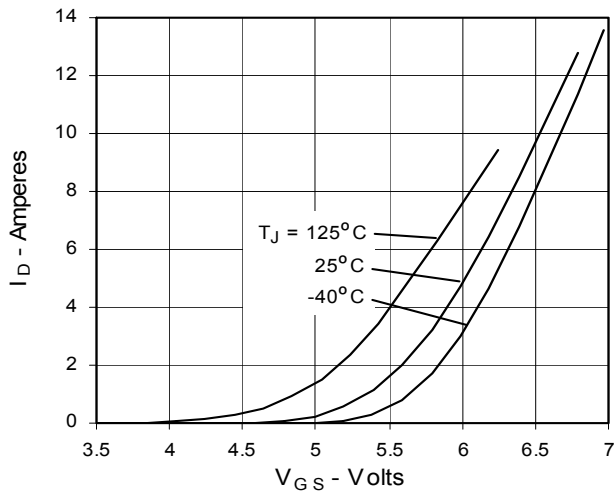


Fig. 8. Transconductance

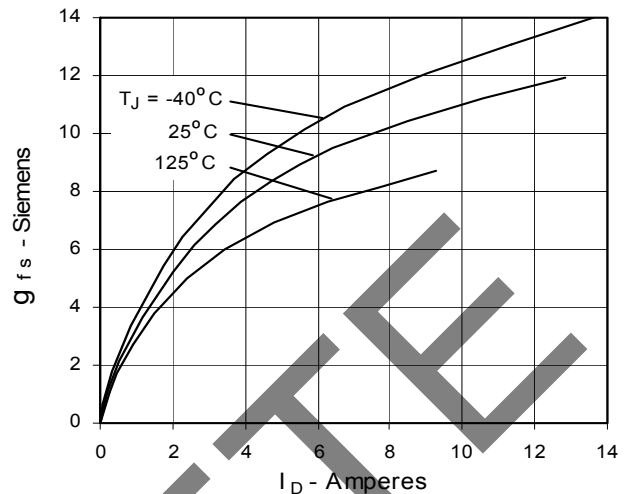


Fig. 9. Source Current vs. Source-To-Drain Voltage

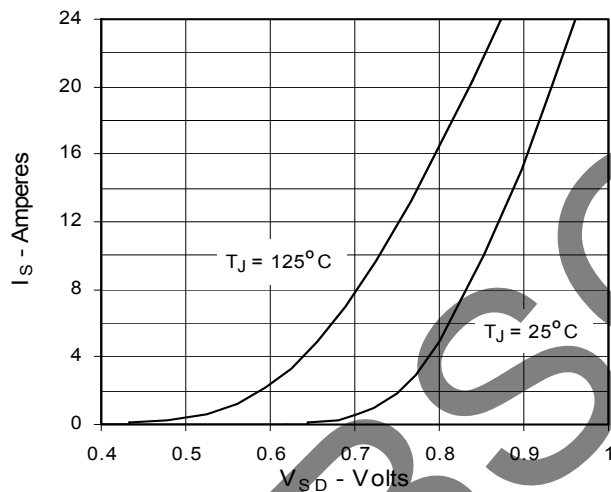


Fig. 10. Gate Charge

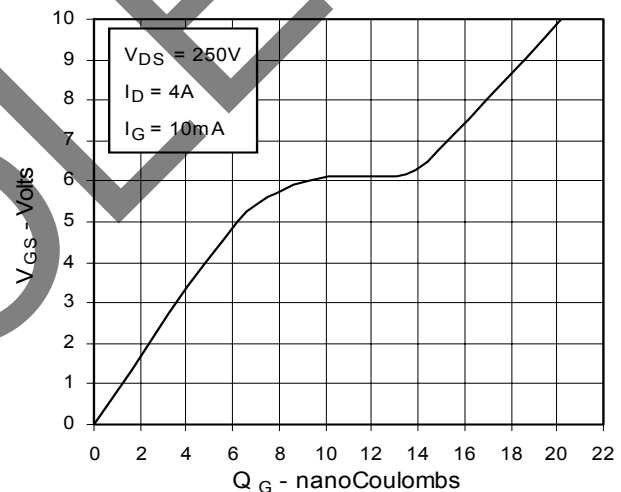


Fig. 11. Capacitance

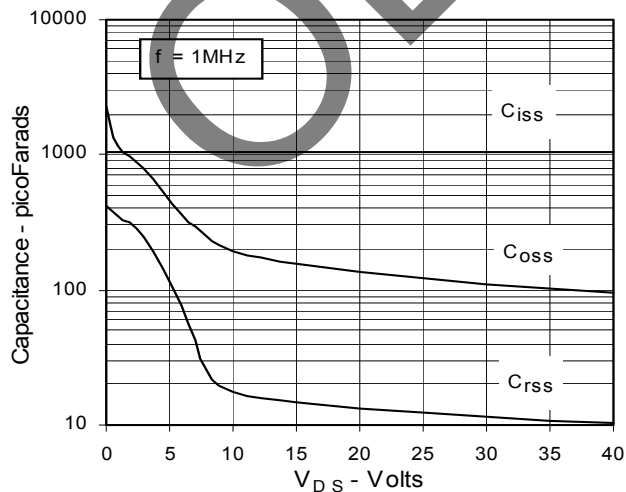


Fig. 12. Forward-Bias Safe Operating Area

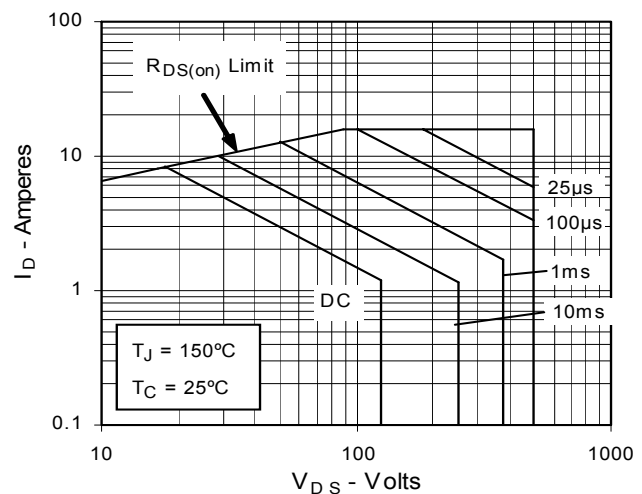


Fig. 13. Maximum Transient Thermal Resistance

